EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	2170	(438/285,287,785).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/07/12 09:20
L2	336	L1 and ((silicon adj1 germanium) SiGe)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/12 09:20
S1	3	("5259881"|"6296711"|"6488777"). PN.	US-PGPUB; USPAT	OR	ON	2006/07/11 12:29
S2	1	"0217378".frpn.	US-PGPUB; USPAT	OR	ON	2006/06/30 16:04
S3	1	"6613684".pn.	US-PGPUB; USPAT	OR	ON	2006/06/30 16:04
S4	7813	atomic adj1 percent	US-PGPUB; USPAT	OR	ON	2006/07/10 07:02
S5	412	S4 and (semiconductor and ((silicon adj1 germanium) SiGe) and ((dielectric k insulator) same high))	US-PGPUB; USPAT	OR	ON	2006/07/10 10:40
S6	200	S4 and (semiconductor and ((silicon adj1 germanium) SiGe) and ((dielectric k insulator) same high)) and oxide and electrode and (CVD ALD sputter$3)	US-PGPUB; USPAT	OR	ON	2006/07/10 10:58
S7	19	(US-20060086977-$ or US-20060071275-$ or US-20050250302-$ or US-20050242406-$ or US-20050199877-$ or US-20050181621-$ or US-20050139872-$ or US-20050099839-$ or US-20050070070-$ or US-20050064322-$ or US-20050045969-$ or US-20040169177-$ or US-20040157455-$ or US-20030098479-$ or US-20030010980-$ or US-20020014625-$).did. or (US-7034337-$ or US-6423632-$ or US-5403434-$).did.	US-PGPUB; USPAT	OR	ON	2006/07/10 09:18

EAST Search History

S8	19	S7 and (semiconductor and ((silicon adj1 germanium) SiGe) and ((dielectric k insulator) same high)) and oxide and electrode and (CVD ALD sputter$3)	US-PGPUB; USPAT	OR	ON	2006/07/10 09:20
S9	19	S7 and (atomic adj1 percent) and (semiconductor and ((silicon adj1 germanium) SiGe) and ((dielectric k insulator) same high)) and oxide and electrode and (CVD ALD sputter$3)	US-PGPUB; USPAT	OR	ON	2006/07/10 16:46
S10	1	("6909151").PN.	US-PGPUB; USPAT	OR	OFF	2006/07/10 09:36
S11	1	S10 and (atomic adj1 percent) and (semiconductor and ((silicon adj1 germanium) SiGe) and ((dielectric k insulator) same high)) and oxide and electrode and (CVD ALD sputter$3)	US-PGPUB; USPAT	OR	ON	2006/07/10 09:37
S12	19	GeHsub(S7)	US-PGPUB; USPAT	OR	ON	2006/07/10 10:40
S13	2866	GeH? GeH GeCl? GeCl	US-PGPUB; USPAT	OR	ON	2006/07/10 10:46
S14	3	S5 and S13	US-PGPUB; USPAT	OR	ON	2006/07/10 10:46
S15	8633	SiH? SiH SiH?Cl? SiHCl	US-PGPUB; USPAT	OR	ON	2006/07/10 10:53
S16	23	S15 and S5	US-PGPUB; USPAT	OR	ON	2006/07/10 10:47
S17	6	S9 and graded	US-PGPUB; USPAT	OR	ON	2006/07/11 16:28
S18	506	(semiconductor and ((silicon adj1 germanium) SiGe) same ((dielectric k insulator) with high)) same oxide	US-PGPUB; USPAT	OR	ON	2006/07/12 09:20
S19	21	(semiconductor and ((silicon adj1 germanium) SiGe) same ((dielectric k insulator) with high)) same oxide same anneal$3	US-PGPUB; USPAT	OR	ON	2006/07/10 11:13
S20	71	(((silicon adj1 germanium) SiGe) same ((dielectric k insulator) with high) same (oxide adj1 layer)) and anneal$3	US-PGPUB; USPAT	OR	ON	2006/07/10 15:58
S21	10145	((silicon adj1 germanium) SiGe) and anneal$3	US-PGPUB; USPAT	OR	ON	2006/07/10 15:59
S22	77	((silicon adj1 germanium) SiGe) same ((dielectric k insulator) with high) same anneal$3	US-PGPUB; USPAT	OR	ON	2006/07/10 15:59

EAST Search History

S23	2	("6909151").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/07/10 16:47
S24	1	S23 and etch$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/10 16:49
S25	1	S23 and etch$3 and dielectric	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/10 16:49
S26	2	("6909151").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/07/11 12:30
S27	1	S26 and anneal	US-PGPUB; USPAT	OR	ON	2006/07/11 12:41
S28	2075	anneal$3 with nitrogen with oxygen	US-PGPUB; USPAT	OR	ON	2006/07/11 12:42
S29	2	("6909151").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/07/11 16:28
S30	874	(semiconductor and ((silicon adj1 germanium) SiGe) same (graded))	US-PGPUB; USPAT	OR	ON	2006/07/11 16:31
S31	737	semiconductor and (((silicon adj1 germanium) SiGe) with graded)	US-PGPUB; USPAT	OR	ON	2006/07/11 16:32
S32	7818	atomic adj1 percent	US-PGPUB; USPAT	OR	ON	2006/07/11 16:33
S33	75	S31 and S32	US-PGPUB; USPAT	OR	ON	2006/07/11 16:38
S34	3	10/683937	US-PGPUB; USPAT	OR	ON	2006/07/11 16:40

EAST Search History

S35	4	(("20020174826") or ("20020174827")).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/07/11 16:41
S36	3	S35 and (((silicon adj1 germanium) SiGe) with graded)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/11 16:41